



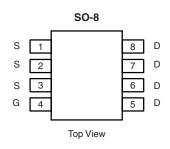
N-Channel 2.5-V (G-S) MOSFET

PRODUCT SUMMARY				
V _{DS} (V)	$R_{DS(on)}\left(\Omega\right)$	I _D (A)		
20	$0.009 \text{ at V}_{GS} = 4.5 \text{ V}$	13.5		
	0.013 at V _{GS} = 2.5 V	11		

FEATURES

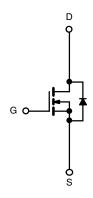
- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET[®] Power MOSFETs
- Compliant to RoHS Directive 2002/95/EC





Ordering Information: Si4466DY-T1-E3 (Lead (Pb)-free)

Si4466DY-T1-GE3 (Lead (Pb)-free and Halogen-free)



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS	$T_A = 25$ °C, unles	ss otherwise r	noted		
Parameter		Symbol	10 s	Steady State	Unit
Drain-Source Voltage		V _{DS}	20		V
Gate-Source Voltage		V_{GS}	± 12		
Continuous Dunin Courant /T 450 °C\	T _A = 25 °C	- I _D	13.5	9.5	Δ.
Continuous Drain Current (T _J = 150 °C) ^a	T _A = 70 °C		10.5	7.5	
Pulsed Drain Current		I _{DM}	50		Α
Continuous Source Current (Diode Conduction) ^a		I _S	2.7	1.36	
Mariana Bana Birata di ad	T _A = 25 °C	- P _D	3.0	1.5	W
Maximum Power Dissipation ^a	T _A = 70 °C		1.9	0.95	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150		°C

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Manifestor Localitan to Applicant	t ≤ 10 s	R _{thJA}	33	42	°C/W
Maximum Junction-to-Ambient ^a	Steady State		70	84	
Maximum Junction-to-Foot (Drain)	Steady State	R _{thJF}	16	21	

Notes:

a. Surface Mounted on FR4 board, $t \le 10 \text{ s.}$

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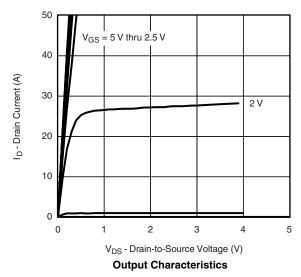
MOSFET SPECIFICATIONS T _J = 25 °C, unless otherwise noted						
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit
Static						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	0.6	1.0	1.4	V
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 12 \text{ V}$			± 100	nA
Zava Cata Valtaga Dvain Curvent	I _{DSS}	V _{DS} = 20 V, V _{GS} = 0 V	1		1	
Zero Gate Voltage Drain Current		$V_{DS} = 20 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55 ^{\circ}\text{C}$			5	μΑ
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge 5 \text{ V}, V_{GS} = 4.5 \text{ V}$	30			Α
	R _{DS(on)}	$V_{GS} = 4.5 \text{ V}, I_D = 13.5 \text{ A}$		0.0055	0.009	
Drain-Source On-State Resistance ^a		$V_{GS} = 2.5 \text{ V}, I_D = 11 \text{ A}$		0.0078	0.013	Ω
Forward Transconductance ^a	9 _{fs}	V _{DS} = 10 V, I _D = 13.5 A		70		S
Diode Forward Voltage ^a	V_{SD}	$I_S = 2.7 \text{ A}, V_{GS} = 0 \text{ V}$		0.70	1.1	V
Dynamic ^b						
Gate Charge	Q_g			40	60	
Gate-Source Charge	Q_{gs}	$V_{DS} = 10 \text{ V}, V_{GS} = 4.5 \text{ V}, I_{D} = 13.5 \text{ A}$		7		nC
Gate-Drain Charge	Q_{gd}			12		
Gate Resistance	R_g		0.5	1.9	3.3	Ω
Turn-On Delay Time	t _{d(on)}			20	30	
Rise Time	t _r	$V_{DD} = 10 \text{ V}, R_{L} = 10 \Omega$		15	25	
Turn-Off Delay Time	t _{d(off)}	$I_D \cong 1 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 6 \Omega$		150	250	ns
Fall Time	t _f			70	110	
Source-Drain Reverse Recovery Time	t _{rr}	$I_F = 2.7 \text{ A}, \text{ dI/dt} = 100 \text{ A/}\mu\text{s}$		55	90	

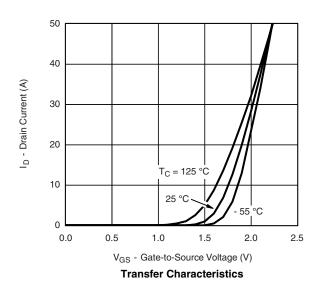
Notes:

- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

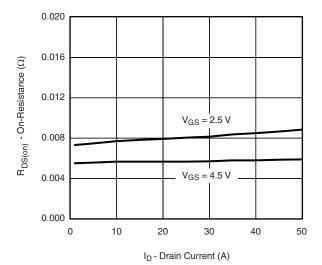




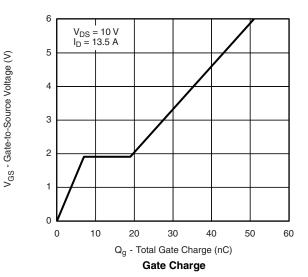




TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



On-Resistance vs. Drain Current



T_J = 150 °C

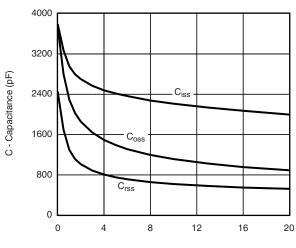
T_J = 150 °C

T_J = 25 °C

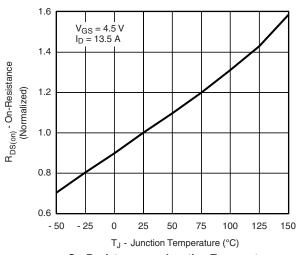
T_J = 25 °C

V_{SD} - Source-to-Drain Voltage (V)

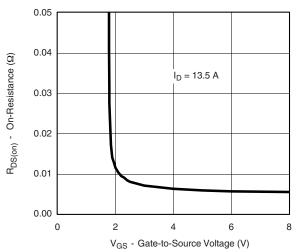
Source-Drain Diode Forward Voltage



V_{DS} - Drain-to-Source Voltage (V) **Capacitance**



On-Resistance vs. Junction Temperature



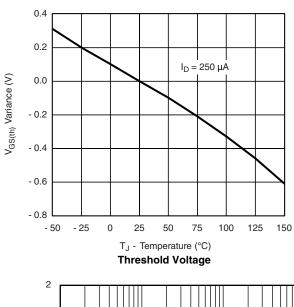
On-Resistance vs. Gate-to-Source Voltage

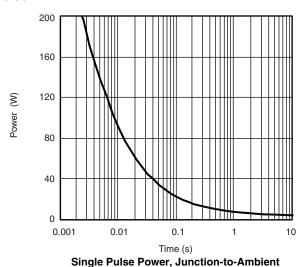
Is - Source Current (A)

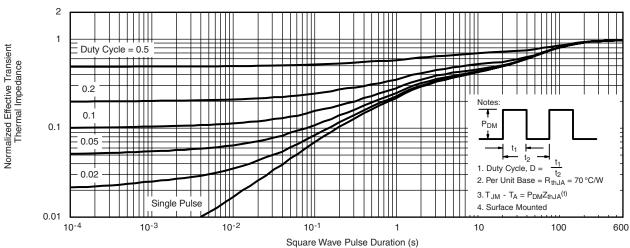
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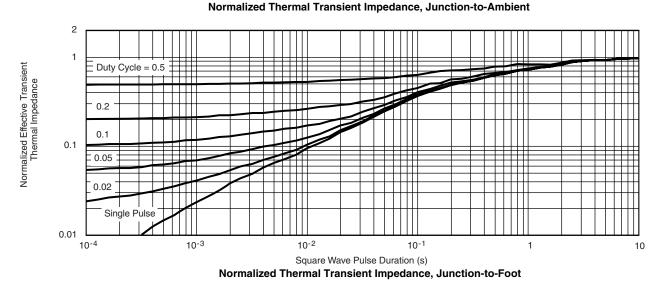
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TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted









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